

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

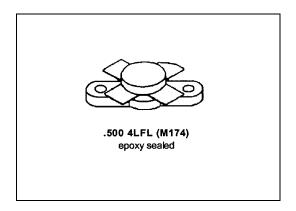
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## MS1051

# RF & MICROWAVE TRANSISTORS WW. Cartasheel 4U. COM HF SSB APLICATIONS

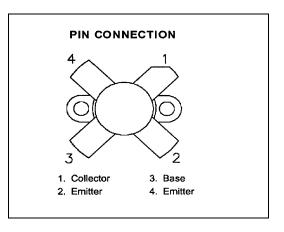
#### **Features**

- 30 MHz
- 12.5 VOLTS
- P<sub>OUT</sub> = 100 WATTS
- G<sub>PE</sub> = 12.0 dB MINIMUM
- IMD = −30 dBc
- GOLD METALLIZATION
- COMMON EMITTER CONFIGURATION



#### **DESCRIPTION:**

The MS1051 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for HF communications. This device utilizes state-of-the-art diffused emitter ballasting to achieve extreme ruggedness under severe operating conditions.



## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	36	V
$V_{\sf CEO}$	Collector-Emitter Voltage	18	V
<b>V</b> <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
<b>I</b> C	Device Current	20	Α
P <sub>DISS</sub>	Power Dissipation	290	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage TEmperature	-65 to +150	°C

#### THERMAL DATA

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	0.6	°C/W
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# ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

## **STATIC**

Symbol	Test Conditions			Value		
			Min.	Typ.	Max.	Unit
<b>BV</b> <sub>CBO</sub>	I <sub>C</sub> = 100mA	I <sub>E</sub> = 0mA	36			V
BV <sub>CES</sub>	I <sub>C</sub> = 100mA	V <sub>BE</sub> = 0V	36			V
BV <sub>CEO</sub>	I <sub>C</sub> = 10mA	I <sub>B</sub> = 0mA	18			V
BV <sub>EBO</sub>	I <sub>E</sub> = 20mA	I <sub>C</sub> = 0mA	4.0			V
I <sub>CES</sub>	V <sub>CE</sub> = 15V	I <sub>C</sub> = 0mA			20	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 5A	20		200	

## **DYNAMIC**

Symbol	Test Conditions		Value				
				Min.	Typ.	Max.	Unit
$\mathbf{P}_{OUT}$	f = 30 MHz	$V_{CE}$ = 12.5 $V$	I <sub>CQ</sub> = 150mA	100			W
G <sub>P</sub>	f = 30 MHz	V <sub>CE</sub> = 12.5 V	I <sub>CQ</sub> = 150mA	11	13		dB
IMD <sub>3</sub> *	<b>P</b> <sub>OUT</sub> = <b>100 W PEP</b>	V <sub>CE</sub> = 12.5 V	I <sub>CQ</sub> = 150mA			-30	dBc
C <sub>OB</sub>	f = 1 MHz	V <sub>CB</sub> = 12.5 V			400		pf
Condition	f1 = 30.000MHz	f2 = 30.001MHz					



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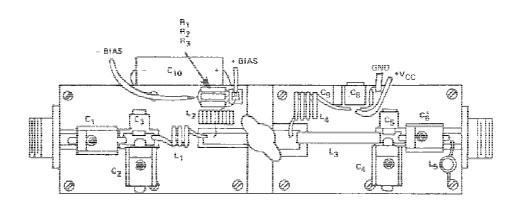
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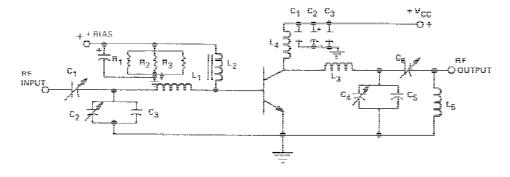
#### **IMPEDANCE DATA**

FREQ	$\mathbf{Z}_{IN}(\Omega)$	$\mathbf{Z}_{\mathtt{CL}}(\Omega)$		
30 MHz	0.57 + j 0.78	0.80 + j 0.43		

 $P_{OUT} = 100 \text{ WPEP}, V_{CE} = 12.5 \text{ V}$ 

### **TEST CIRCUIT**





9 - 180pF Arco 463 C2 5 - 380pF Arco 465 C3 200pF Arco 465 170pF Arco 469 C4, C6:

C7 0.1μF Ceramic Disc C5, C8: 1000pF Unelco

10μF Electrolytic, 35Vdc 1000μF Electrolytic, 35Vdc C9 C10

L1 2 1/2 Turns, #14 AWG, I.D. Loose Wound 16 Turns, #16 AWG, Enameled Wire on Micrometals Torroid #T-94 L2

Copper Strap 1/4" Widht, Length 1 1/2, L3

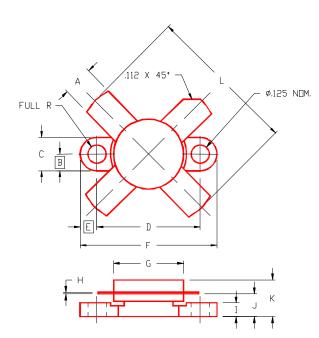
Height 1/2"
4 Turns, #16 AWG, Enameled Wire 3/8" I.D.
5 Turns, #18 AWG on 1/4" I.D. Coil Form
Length 1/2", Ferrite Slug L4

R1, R2, R3 : 1.5 Ohm, 1 Watt Carbon



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## **WPAGKAGE** MECHANICAL DATA



#### PACKAGE STYLE M174

		MIN1MUM	MAXIMUM	Π		MIN]MUM	MAX]MUM
		INCHES/MM	INCHE2/MM	Ш		INCHES/MM	INCHE S/MM
	Α	.220/5,59	.230/5,84	П	I	.090/2,29	.110/2,79
	В	.125/3,18			J	.160/4,06	.175/4,45
	С	.245/6,22	.255/6,48	Π	К		.280/7,11
	D	.720/18,28	.730/18,54	Π	L		1.050/26,67
	Ε	.125/3,18					
	F	.970/24,64	.980/24,89	Π			
	G	.495/12,57	.505/12,83	Π			
i	Н	.003/0,08	.007/0,18				